

**Cascadable Amplifier
10 to 1500 MHz**

A29-1/ SMA29-1

V3

Features

- HIGH OUTPUT POWER: +22 dBm (TYP.)
- HIGH THIRD ORDER I.P.: +32 dBm (TYP.)

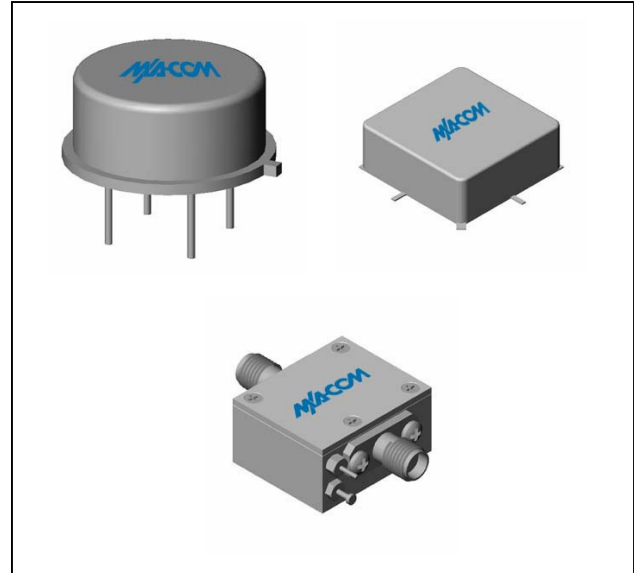
Description

The A29-1 RF amplifier is a discrete thin film hybrid design, which incorporates the use of thin film manufacturing processes for accurate performance and high reliability.

This single stage bipolar transistor feedback amplifier design displays impressive performance over a broadband frequency range. An active DC biasing network is used for temperature-stable performance, in addition to an RF Choke, used for power supply decoupling.

Both TO-8 and Surface Mount packages are hermetically sealed, and MIL-STD-883 environmental screening is available.

Product Image



Ordering Information

Part Number	Package
A29-1	TO-8
SMA29-1	Surface Mount
CA29-1	SMA Connectorized

Electrical Specifications: $Z_0 = 50\Omega$, $V_{CC} = +15 V_{DC}$

Parameter	Units	Typical	Guaranteed	
		25°C	0° to 50°C	-54° to +85°C*
Frequency	MHz	10-1600	10-1500	10-1500
Small Signal Gain (min)	dB	9.0	8.5	7.5
Gain Flatness (max)	dB	±0.2	±0.5	±1.0
Reverse Isolation	dB	14		
Noise Figure (max)	dB	5.5	6.5	7.0
Power Output @ 1 dB comp. (min)	dBm	22.0	20.0	19.0
IP3	dBm	+32		
IP2	dBm	+49		
Second Order Harmonic IP	dBm	+57		
VSWR Input / Output (max)		1.6:1 / 1.6:1	1.9:1 / 1.9:1	2.0:1 / 2.0:1
DC Current @ 15 Volts (max)	mA	90	94	99

Absolute Maximum Ratings

Parameter	Absolute Maximum
Storage Temperature	-62°C to +125°C
Case Temperature	+125°C
DC Voltage	+17 V
Continuous Input Power	15.5 dBm
Short Term Input power (1 minute max.)	100 mW
Peak Power (3 µsec max.)	0.5 W
"S" Series Burn-In Temperature (case)	+125°C

Thermal Data: $V_{CC} = +15 V_{DC}$

Parameter	Rating
Thermal Resistance θ_{jc}	100°C/W
Transistor Power Dissipation P_d	0.966 W
Junction Temperature Rise Above Case T_{jc}	+96°C

* Over temperature performance limits for part number CA29-1, guaranteed from 0°C to +50°C only.

